

QUERY CONTROL FORM		RTIS USE ONLY	
Application No. <u>10/777,071</u>	Prepared by <u>ewc</u>	Tracking Number <u>05966851</u>	
Examiner-GAU <u>Mulpuvi</u>	Date <u>8/23/04</u>	Week Date <u>6-14-04</u>	
<u>2812</u>	No. of queries <u>- 1 -</u>	<u>IFW</u>	

JACKET			
a. Serial No.	f. Foreign Priority	k. Print Claim(s)	p. PTO-1449
b. Applicant(s)	g. Disclaimer	l. Print Fig.	q. PTOL-85b
c. Continuing Data	h. Microfiche Appendix	m. Searched Column	r. Abstract
d. PCT	i. Title	n. PTO-270/328	s. Sheets/Figs
e. Domestic Priority	j. Claims Allowed	o. PTO-892	t. Other

SPECIFICATION	MESSAGE
a. Page Missing	<p>Instructions/insertions on page 3 on NOA 6-02-04 cannot be completed</p> <p>Please check tagged copy of amendment (attached).</p> <p>Thank you</p> <p>ewc</p>
b. Text Continuity	
c. Holes through Data	
d. Other Missing Text	
e. Illegible Text	
f. Duplicate Text	
g. Brief Description	
h. Sequence Listing	
i. Appendix	
j. Amendments	
k. Other	
CLAIMS	
a. Claim(s) Missing	
b. Improper Dependency	
c. Duplicate Numbers	
d. Incorrect Numbering	
e. Index Disagrees	
f. Punctuation	
g. Amendments	
h. Bracketing	
i. Missing Text	
j. Duplicate Text	
k. Other	
	initials
	RESPONSE
	initials

In claim 11, line 5 replace "a" with ~~the~~

⁵
In claim 12, line 6 replace "a" with ~~the~~

⁹
In claim 12, line 10 replace "a" with ~~the~~

In claim 13, line 6 replace "a" with ~~the~~

In claim 14, line 9 replace "a" with ~~the~~

In claim 14, line 11 add ~~—~~, wherein the semiconductor material

In claim 14, line 12 replace "a" with ~~the~~

In claim 15, line 10 replace "a" with ~~the~~

In claim 15, line 10 delete "on a plate member disposed"

In claim 15, line 16 after "film" add ~~—~~, wherein the semiconductor film

In claim 15, line 17 replace "a" with ~~the~~

In claim 15, line 17 after "substrate" add ~~—, and—~~

In claim 15, line 18 replace "a" with ~~the~~

The following is an examiner's statement of reasons for allowance: Prior art neither teach nor suggest forming layered film with first second and third compound semiconductor layers, wherein second compound layer comprises Al-containing material (as recited in claim 1, 10) or first cladding layer active layer and second cladding layer and at least first cladding layer comprises Al-containing material (as recited in claim 10 and 15), selectively etching layered film and to form three-dimensional structure or stripe having sidewall portion in which Al-containing material is exposed to at least part of the side wall portion, placing three-dimensional or stripe